

# **Structured Electronic Design**

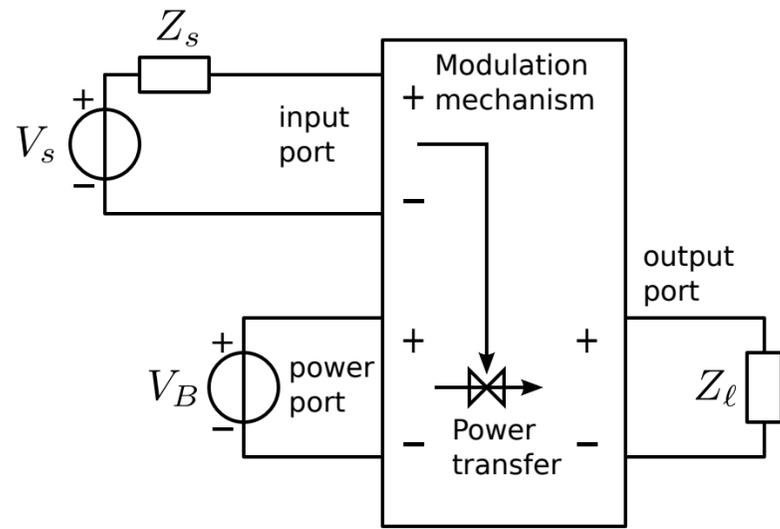
EE4109

Course program

*Anton J.M. Montagne*

# Principle of amplification and biasing

Modulation of power transfer from power source to the load by the signal source



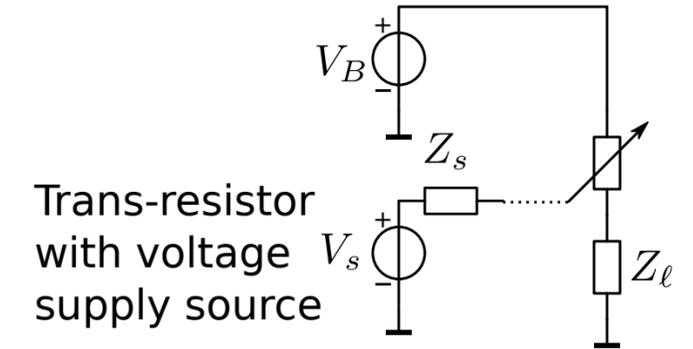
Modulation of a current through a passive device:

A. Search for a device:

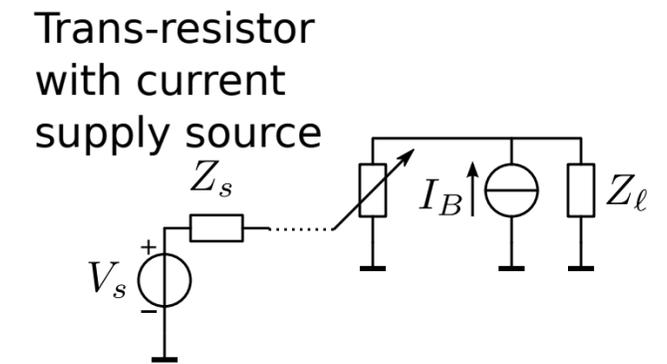
1. Two-terminal device with nonlinear v-i characteristic
2. Two-port device with output v-i characteristic controlled by its input voltage or current

C. Create a current through this device

1. Apply a bias source at the output

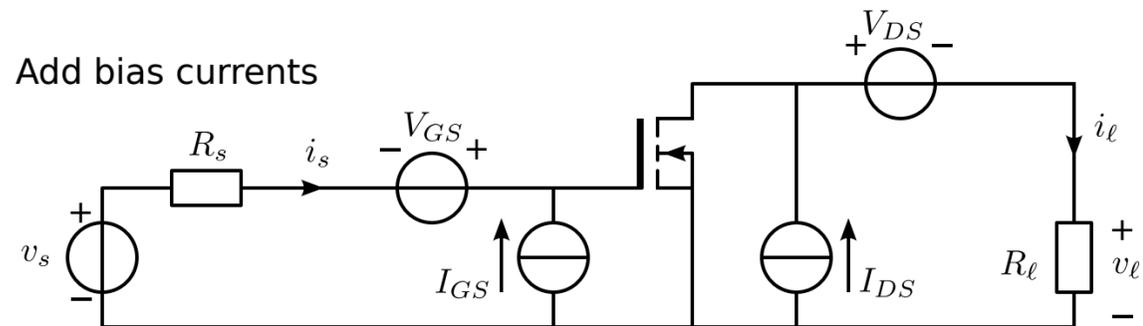


Trans-resistor with voltage supply source

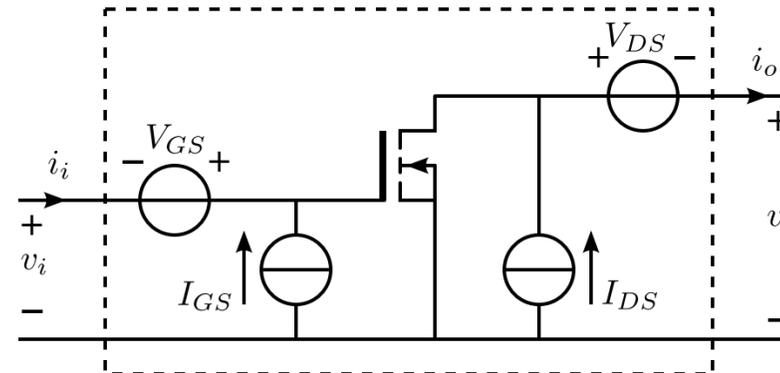


Trans-resistor with current supply source

Add bias currents

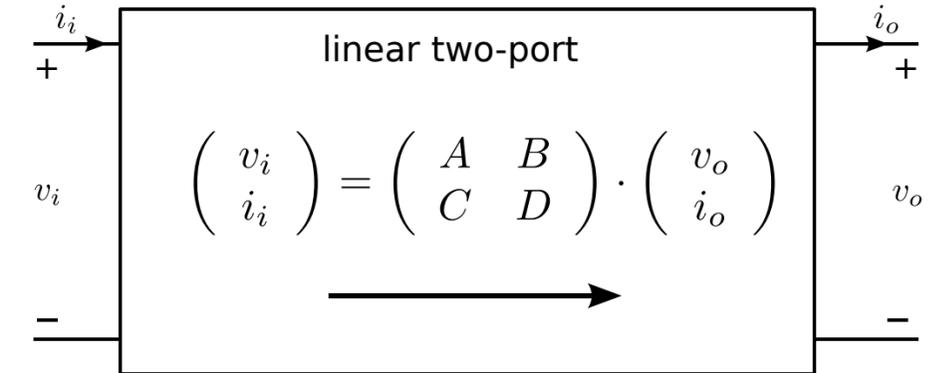


No bias currents flow through the source and the load  
 $(v_s, v_l), (v_s, i_l), (i_s, v_l), (i_s, i_l)$  characteristics pass through the origin



Biased amplifier stage  
 Bias power delivered by  $I_{GS}$  and  $I_{DS}$

Linearization in the operating point:

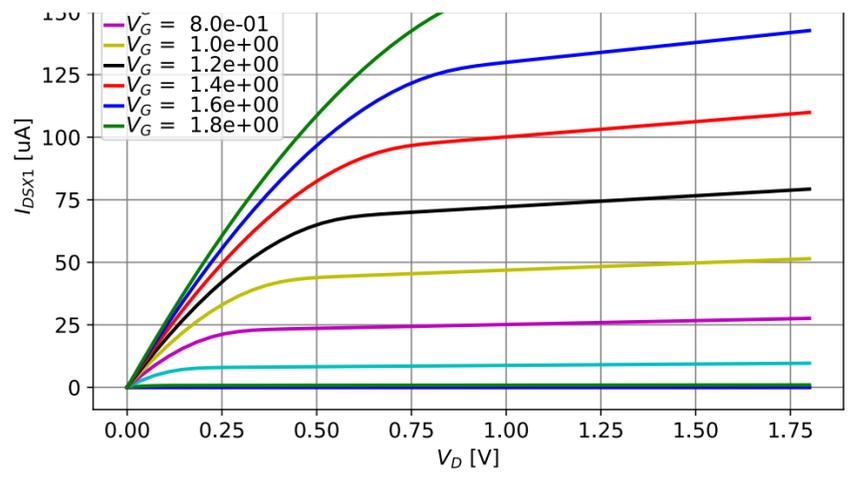
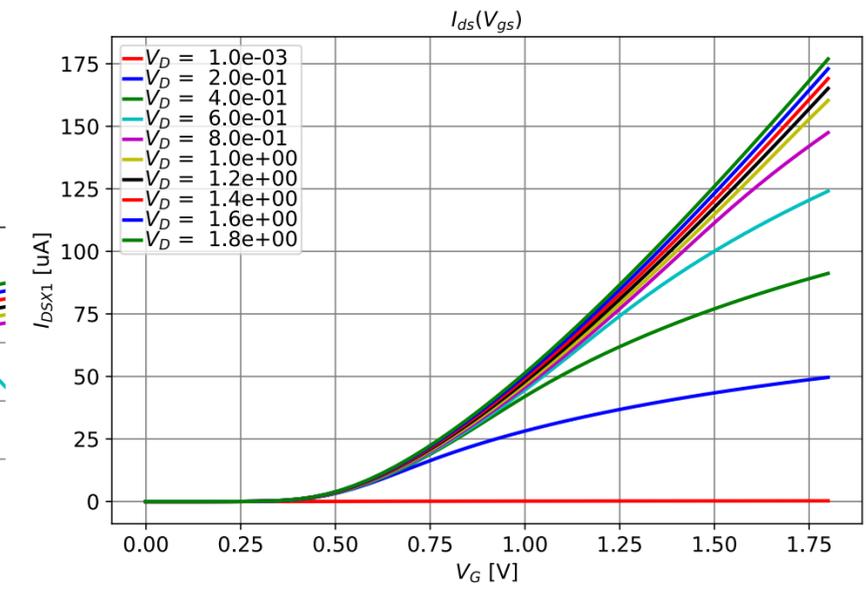
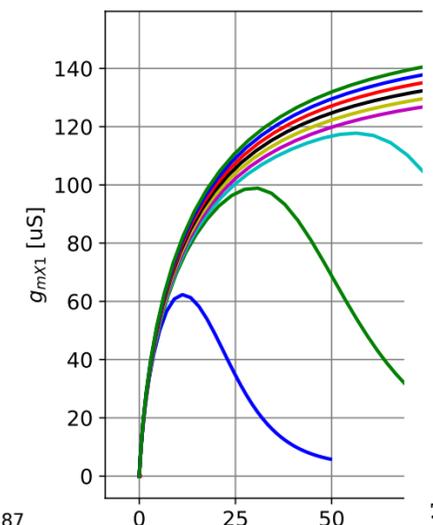
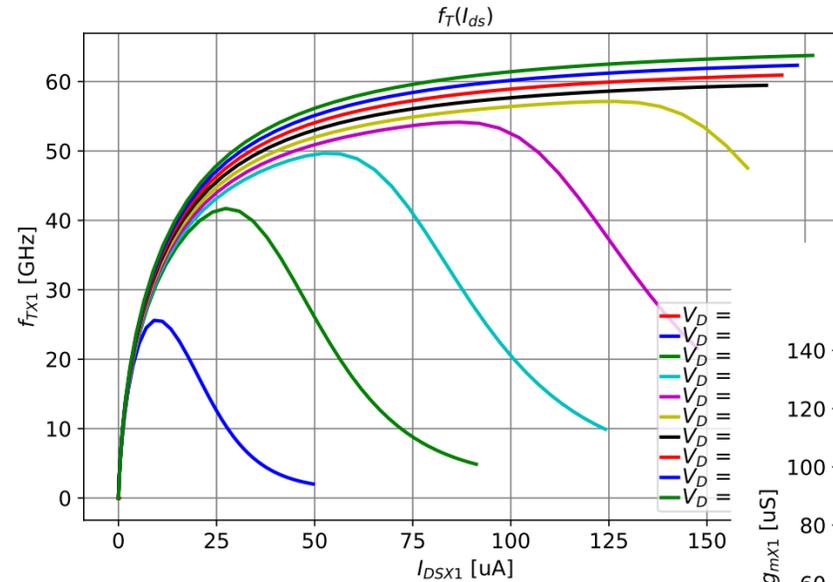


Maximum available power gain of a unilateral linear resistive two-port:

$$P_{av,max} = \frac{1}{4AD}$$

# Amplifying devices

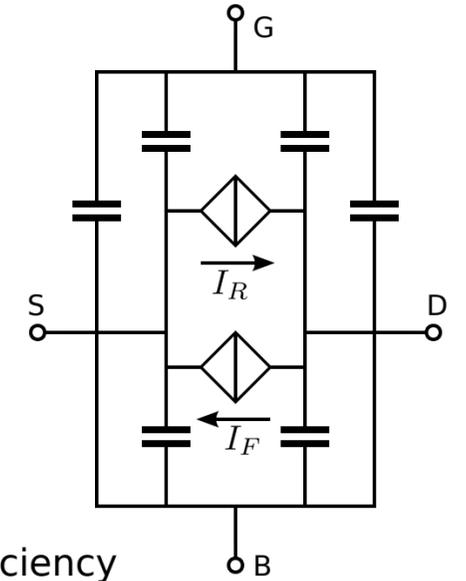
Estimate amplifying capabilities and limitations from device characteristics, geometry and operating conditions



```
.model C18nmos nmos (
+level=49
+noimod=1 version=3.1 tnom=27 tox=4.1E-9 xj=1E-7 nch=2.3549E17 vth0=0.362587
+k1=0.5865832 k2=4.152205E-3 k3=1E-3 k3b=2.1824687 w0=1E-7 nlx=1.795622E-7
+dvt0w=0 dvt1w=0 dvt2w=0 dvt0=1.746117 dvt1=0.4409233 dvt2=-3.663487E-4
+u0=262.117234 ua=-1.386325E-9 ub=2.284255E-18 uc=5.506514E-11 vsat=1.04174E5 a0=1.9287698
+ags=0.416466 b0=-1.536637E-9 b1=-1E-7 keta=-7.111387E-3 a1=6.573435E-4 a2=0.8808358
+rds=112.5093924 prwg=0.494777 prwb=-0.2 wr=1 wint=7.098292E-9 lint=1.120392E-8
+xl=-2E-8 xw=-1E-8 dwg=-3.812756E-9 dwb=8.690068E-9 voff=-0.0878502 nfactor=2.2975194
+cit=0 cdsc=2.4E-4 cdsd=0 cdsb=0 eta0=3.116078E-3 etab=1
+dsub=0.0226021 pclm=0.7222753 pdiblc1=0.2160258 pdiblc2=2.237807E-3 pdiblc3=0.1 drout=0.8036712
+pscbel=5.434136E8 psdbe2=1e-3 pvag=1e-12 delta=0.01 rsh=6.8 mobmod=1 prt=0 ute=-1.5
+kt1=-0.11 kt1l=0 kt2=0.022 ua1=4.31E-9 ub1=-7.61E-18 uc1=-5.6E-11 at=3.3E4 wl=0 wln=1 ww=0
+wwn=1 wwl=0 ll=0 lln=1 lw=0 lwn=1 lwl=0 capmod=2 xpart=0.5
+cgdo=6.99E-10 cgso=6.99E-10 cgbo=1E-12 cj=9.840057E-4 pb=0.7342005 mj=0.3623465
+cjsw=2.405513E-10 pbsw=0.4681508 mjsw=0.1 cjswg=3.3E-10 pbswg=0.4681508 mjswg=0.1
+cf=0 pvth0=-7.11401E-4 prdsw=-0.6661763 pk2=5.920718E-4 wketa=2.148339E-4 lketa=-0.0151118
+pu0=3.3563216 pua=-1.30682E-11 pub=0 pvsat=1.25639E3 peta0=1E-4 pketa=6.507934E-4
+kf=4.5E-29)
```

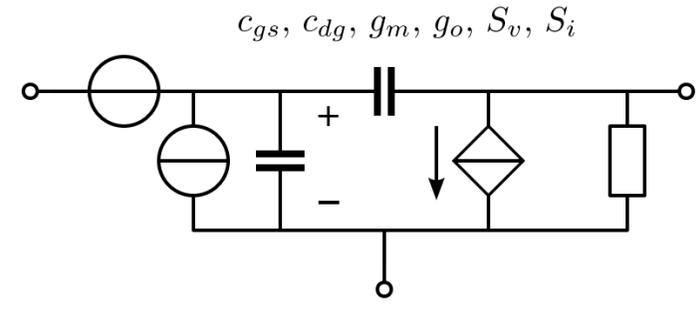
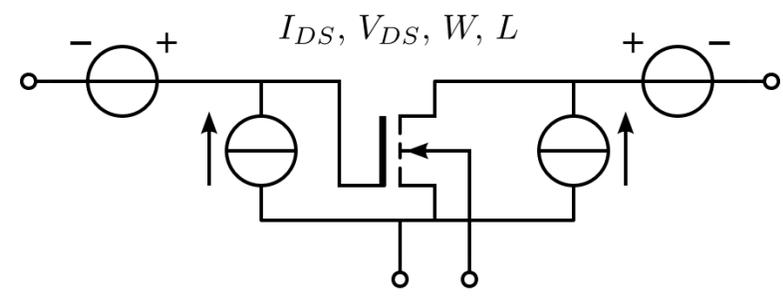
## EKV model

- Cut-off frequency
- Inversion coefficient
- Transconductance efficiency
- Critical inversion coefficient
- 1/f noise corner frequency

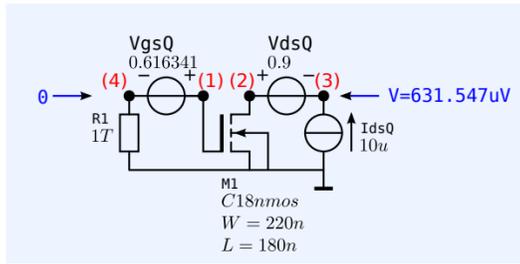


```
.subckt CMOS18N drain gate source bulk W={W} L={L} ID={ID}
* EKV model of transistor without bulk resistances
* Voltage dependency of bulk capacitances not modeled
* Operating in forward saturation region
*
M1 drain gate source bulk CMOS18N

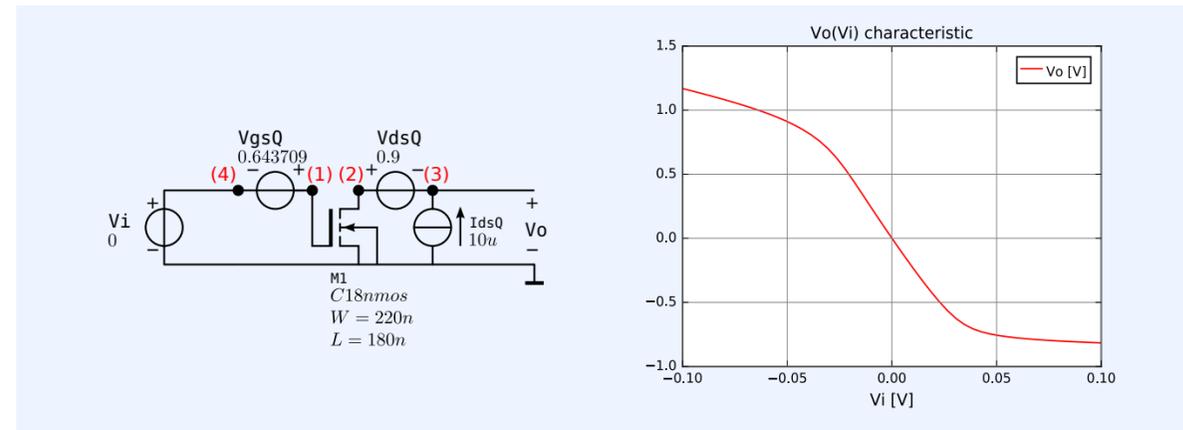
.model CMOS18N M
+ gm = {g_m}
+ go = {g_o}
+ gb = {g_b}
+ cgs = {c_gs}
+ cdg = {c_dg}
+ cgb = {c_gb}
+ cdb = {c_db}
+ csb = {c_sb}
* Parameters will be substituted if simType has been set to "numeric"
.param
* device equations EKV model
* See Binkley: "Tradeoffs and Optimization in Analog CMOS Design"
+ IC_CRIT = {1/(4*(N_s_N18*U_T)*(Theta_N18+1/L/E_CRIT_N18))^2}
+ g_m = {ID/(N_s_N18*U_T*sqrt(IC*(1+IC/IC_CRIT))+0.5*sqrt(IC*(1+IC/IC_CRIT))+1)}
+ g_o = {ID/VAL_N18/L}
+ g_b = {(N_s_N18-1)*g_m}
+ c_gs = {2/3*W*L*C_OX_N18 + CGSO_N18*W}
+ c_dg = {CGSO_N18*W}
+ c_gb = {CGBO_N18*2*L+(N_s_N18-1)/N_s_N18*C_OX_N18*W*L/3}
+ c_db = {CJB0_N18*W*LDS_N18}
+ c_sb = {CJB0_N18*W*LDS_N18}
+ IC = {ID*L/W/I_0_N18}
+ V_GS = {2*N_s_N18*U_T*ln(exp(sqrt(IC))-1)+Vth_N18}
+ f_T = {g_m/2/pi/c_iss}
+ c_iss = {c_gs+c_dg+c_gb}
.ends
```



# CS stage static and dynamic behavior



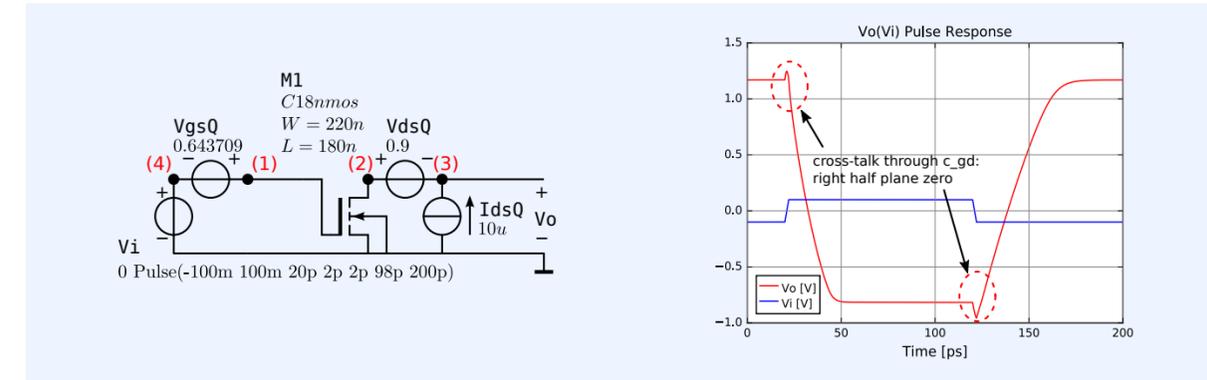
biased stage



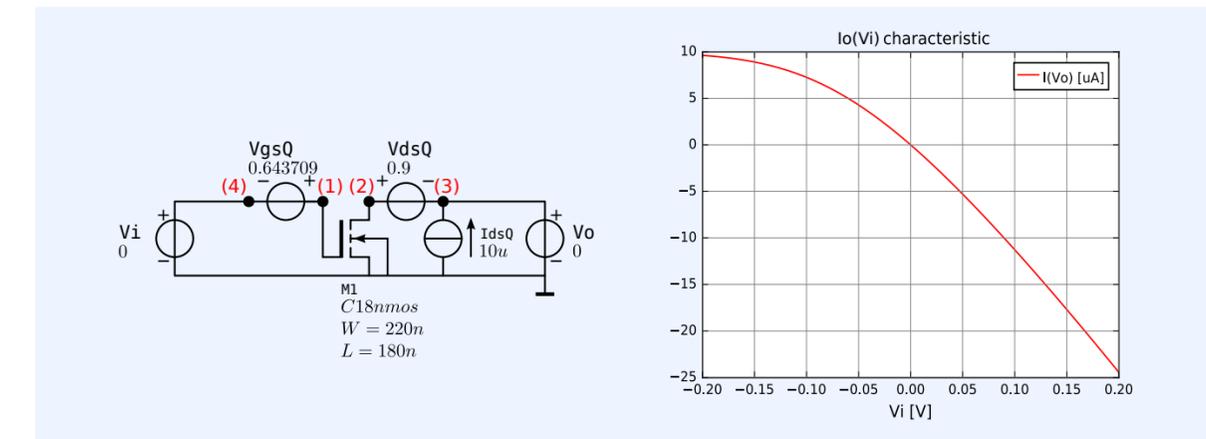
static voltage drive capability

Study behavior

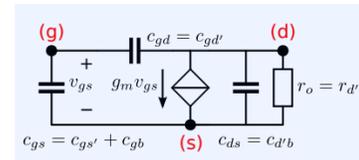
Find design parameters for performance aspects



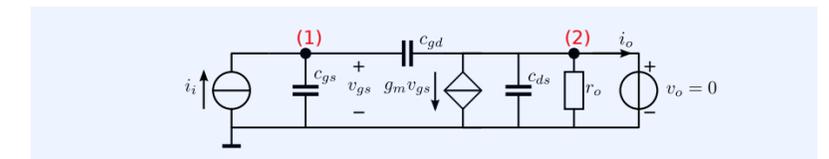
dynamic voltage drive capability



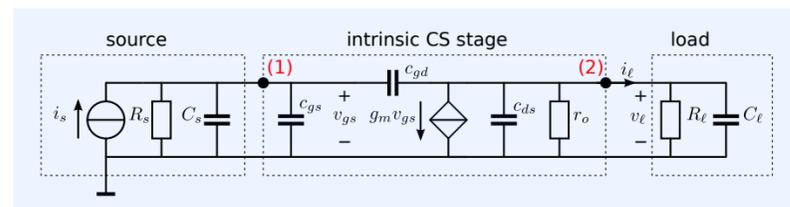
static current drive capability



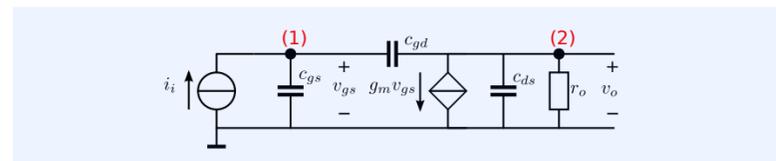
small-signal model



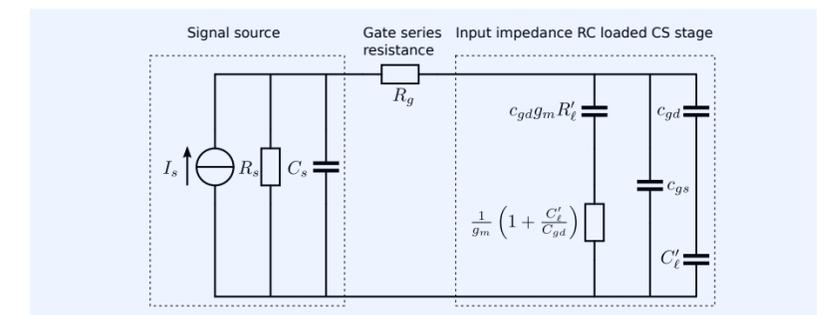
small-signal current gain



small-signal source-to-load transfer



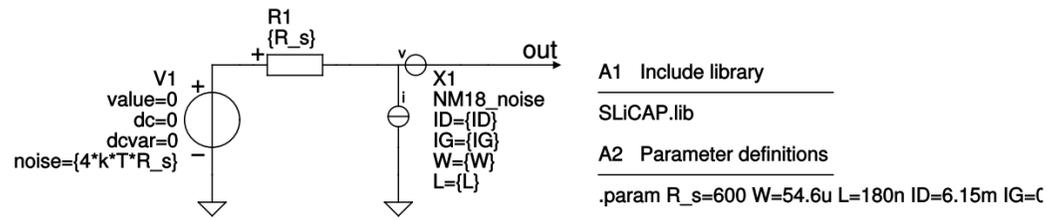
small-signal transimpedance



small-signal voltage driven

# CS stage stationary noise behavior

## Circuit Data



### Netlist: CS stage resistive noise

```

"CS stage resistive noise"
* gnetlist -q -g spice-noqsi -o CSresNoise.net CSresNoise.sch
* SPICE file generated by spice-noqsi version 20130710
* Send requests or bug reports to jpd@noqsi.com
.INCLUDE SLICAP.lib
X1 1 0 out NM18_noise ID={ID} W={W} L={L} IG={IG}
R1 2 1 {R_s}
V1 2 0 V value=0 dc=0 dcvar=0 noise={4*k*T*R_s}
.param R_s=600 W=54.6u L=180n ID=6.15m IG=0
.end
    
```

### Operating parameters

Device width:

$$W = 5.46 \cdot 10^{-5} \quad (1)$$

Drain current for operation at critical inversion:

$$I_D = 0.006169 \quad (2)$$

The effective noise resistance  $R_N$  equals:

$$R_N = 52.39 \quad (3)$$

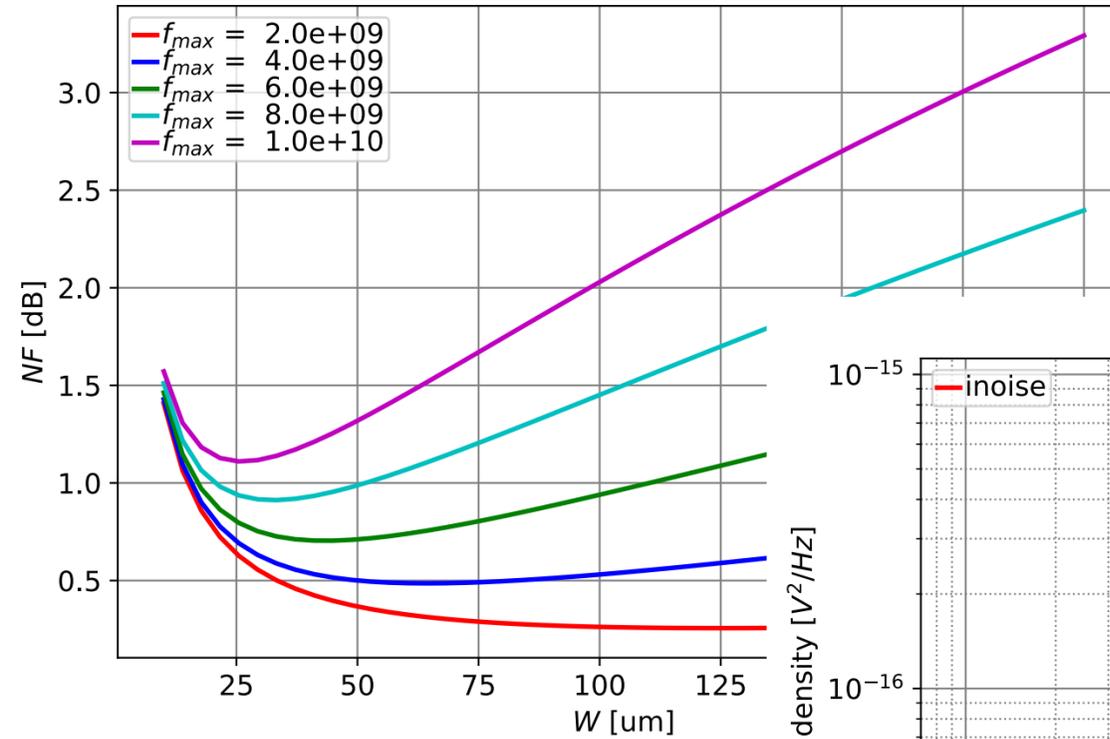
The cut-off frequency  $f_T$  equals:

$$f_T = 3.577 \cdot 10^{10} \quad (4)$$

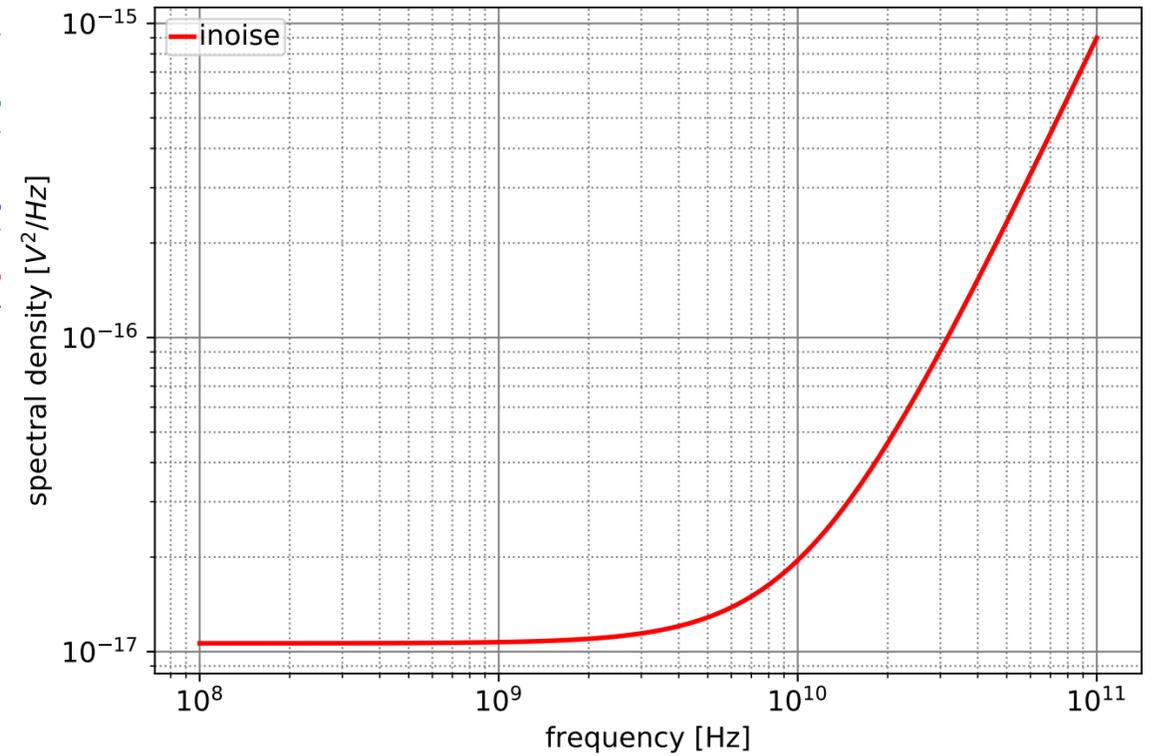
Study noise behavior for various source types

Find design parameters and show stopper values

Noise Figure versus width,  $f_{min} = 200\text{MHz}$



Source-referred noise spectrum



## Find design parameters input and output stage

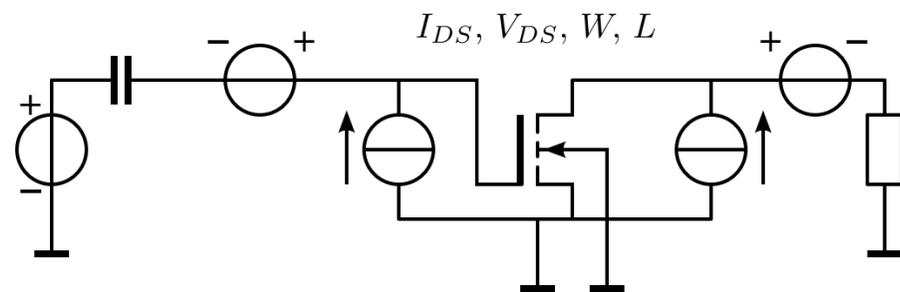
Static and dynamic voltage and current drive capability

Range for drain current, width and length

Noise performance

Range for drain current, voltage, width and length

## If overlap, is single-stage solution feasible?



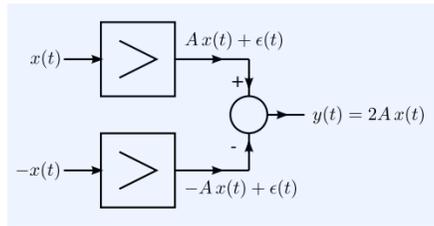
Gain accuracy?  
Noise performance?  
Drive capability?  
Weak nonlinearity?



If OK implement biasing



# Balanced CS stages

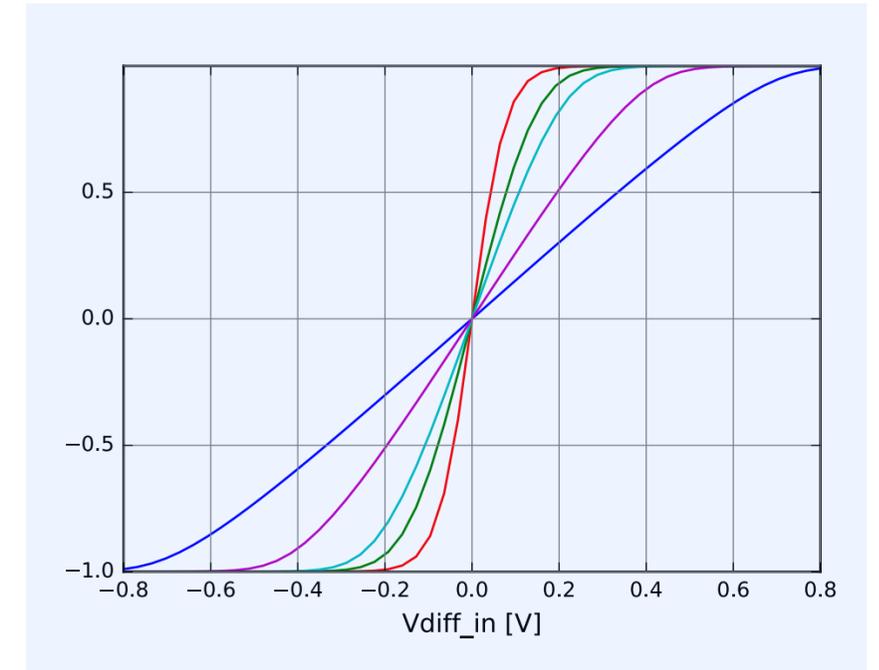
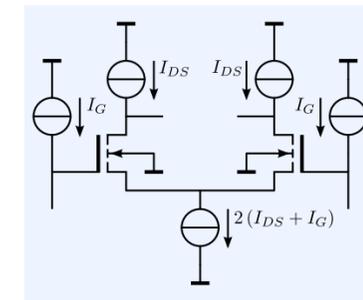
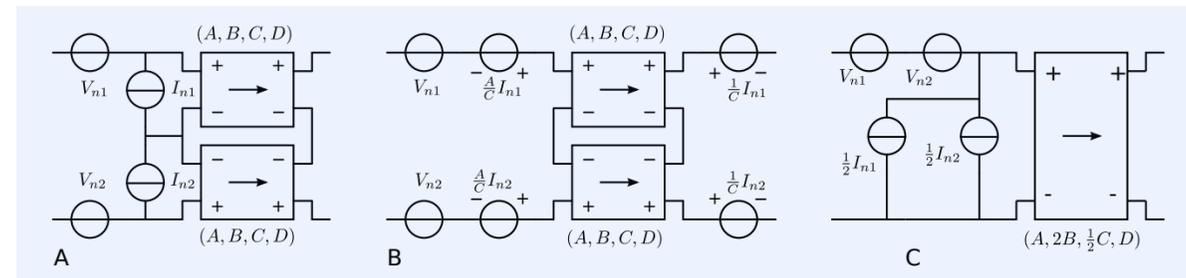
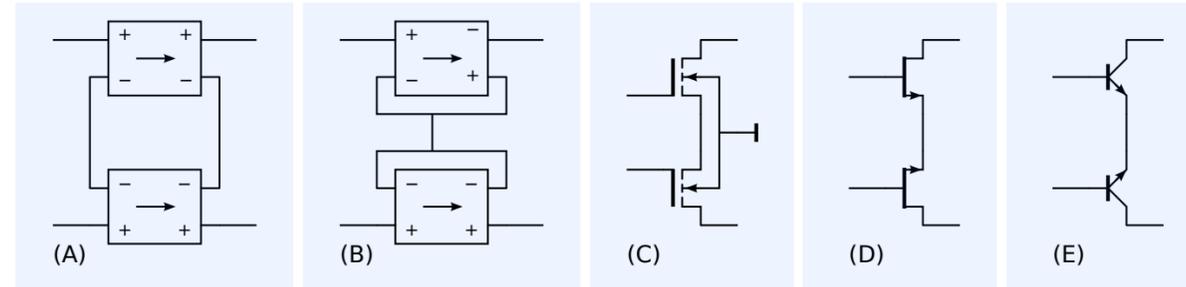
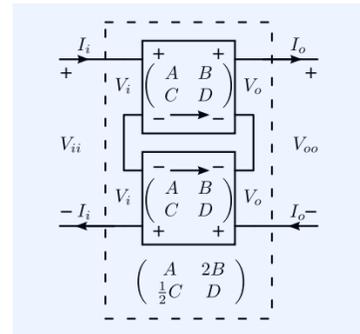


Learn how to generate balanced configurations

Learn about error-reduction capabilities of balancing

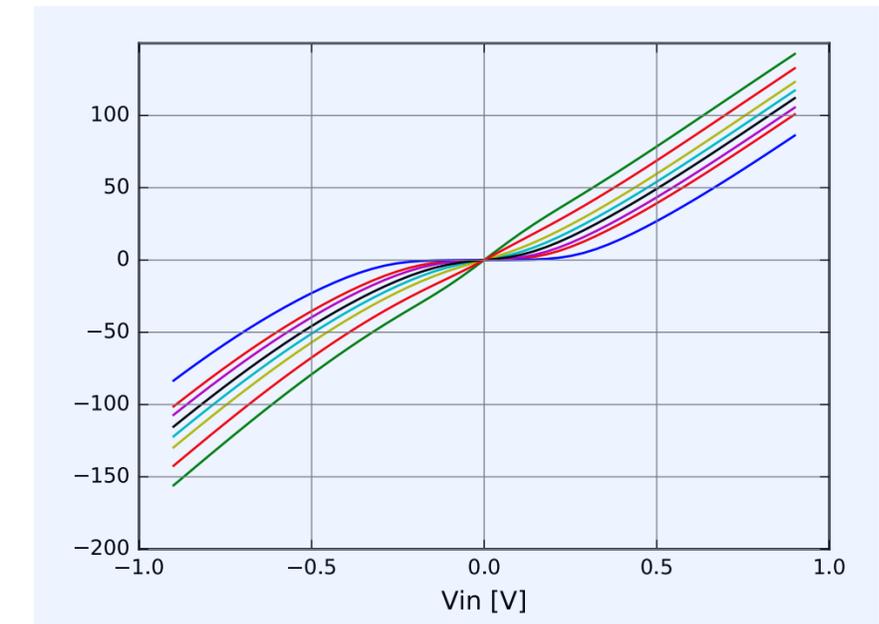
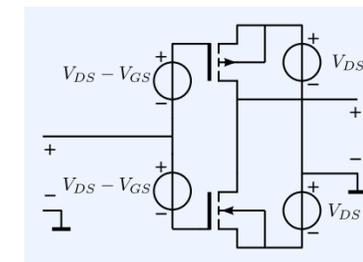
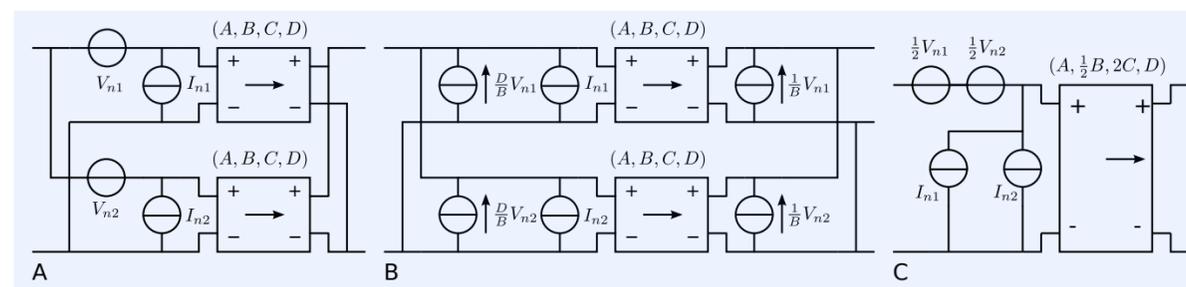
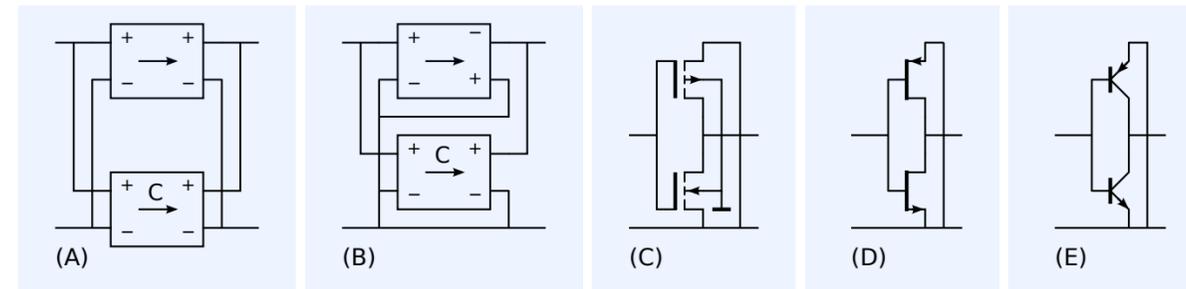
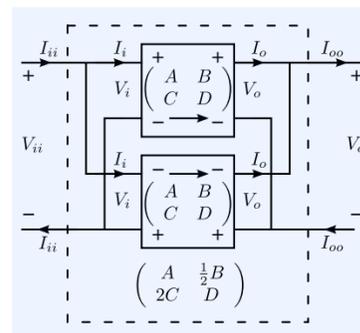
Learn how to relate amplifying capabilities and limitations of balanced configurations to those of unbalanced configurations

Anti-series connection  
Differential pair



Compressing odd characteristic

Complementary-parallel  
connection  
Push-pull stage

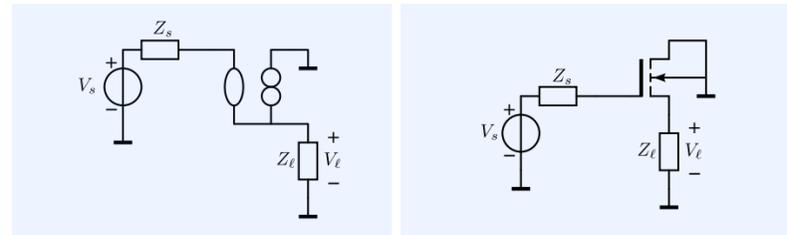
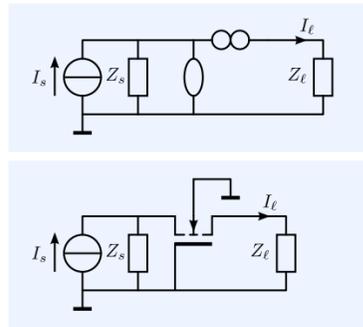
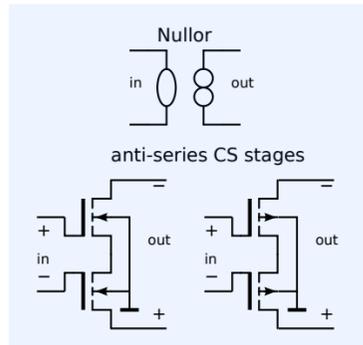
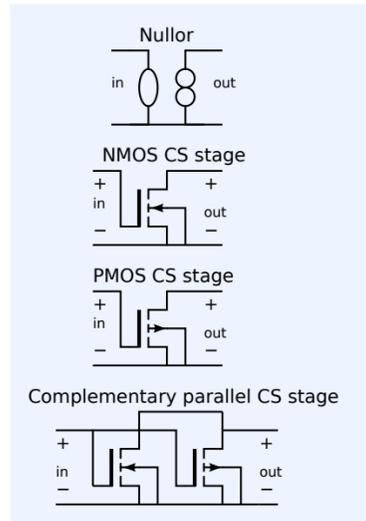


Expanding odd characteristic

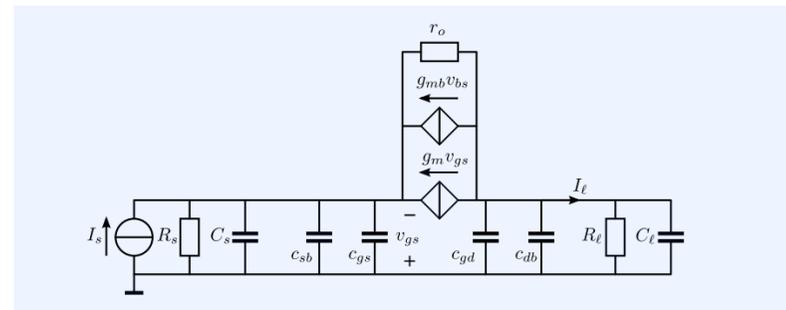
# Feedback stages

Learn to predict the behavioral changes resulting from application of negative feedback

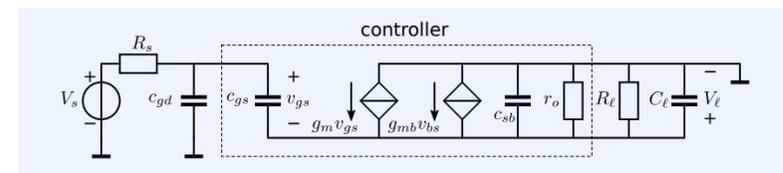
Unbalanced or balanced stages applied as controller in feedback amplifiers



Voltage follower (CD stage)



Current follower (CG stage)

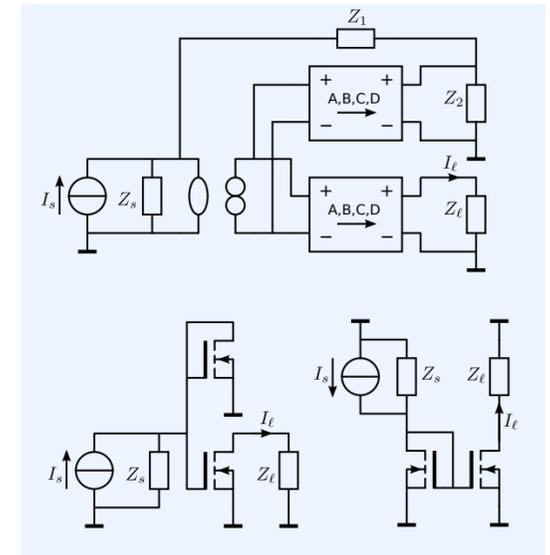


asymptotic-gain feedback model

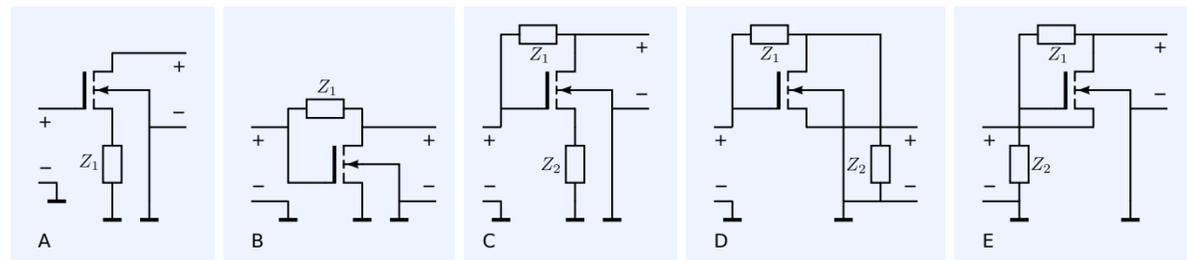
Bandwidth and phantom-zero compensation

```
>> CDcompM18
GAIN
DC value = 7.281e-01
Poles:
  RealPart  ImagPart  Frequency  Q
-----
p_1 -9.2226e+08  1.1702e+09  1.49e+09  0.80779
p_2 -9.2226e+08 -1.1702e+09  1.49e+09  0.80779
Zeros:
  RealPart  ImagPart  Frequency  Q
-----
z_1 -1.3667e+10  0  1.3667e+10  0
>>
```

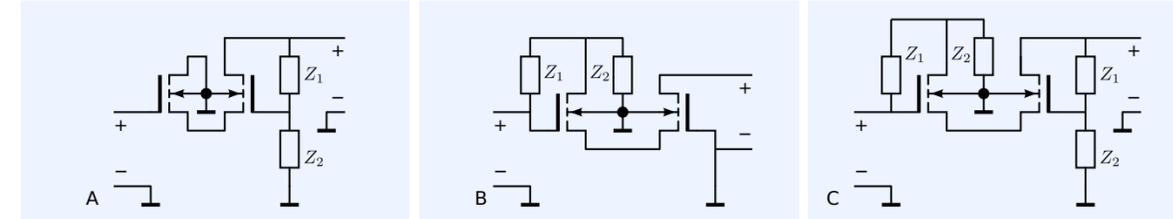
Indirect feedback stages  
Current mirror



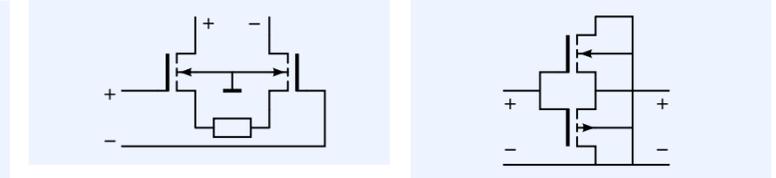
Passive feedback stages; unbalanced controller



Passive feedback stages; balanced controller

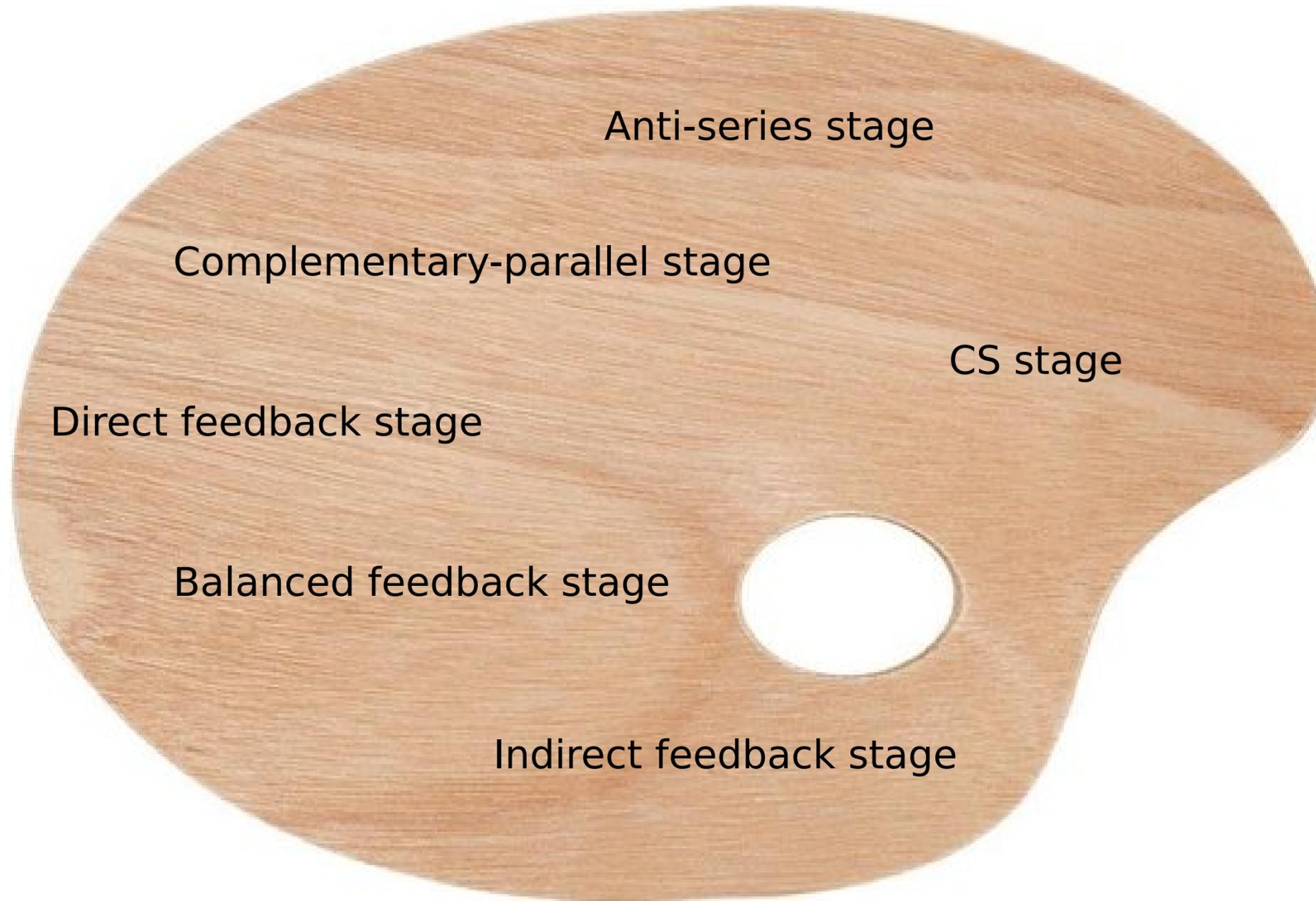


Balanced feedback stages



# Multiple-stage active antenna

## Cascade connection of various types of stages

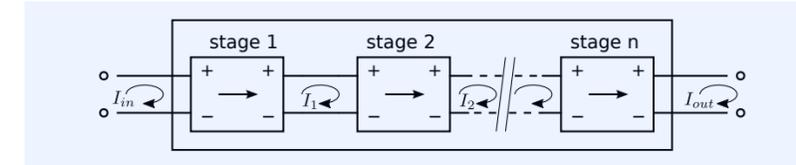


# Feedback amplifiers with multiple-stage controller

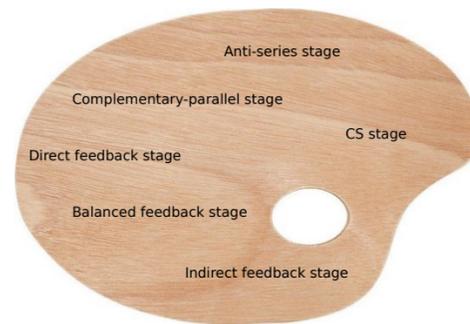
How many stages?

$$n = \frac{m \log f_H - \log LP_1}{\log \frac{f_T}{f_H}}$$

How to interconnect the stages?



What type of stages?



What type of input stage?

What type of output stage?

What type of intermediate stages?

How to reduce the interaction between stages?



Maximization of contribution to loop gain-poles product

Minimization of Miller effect

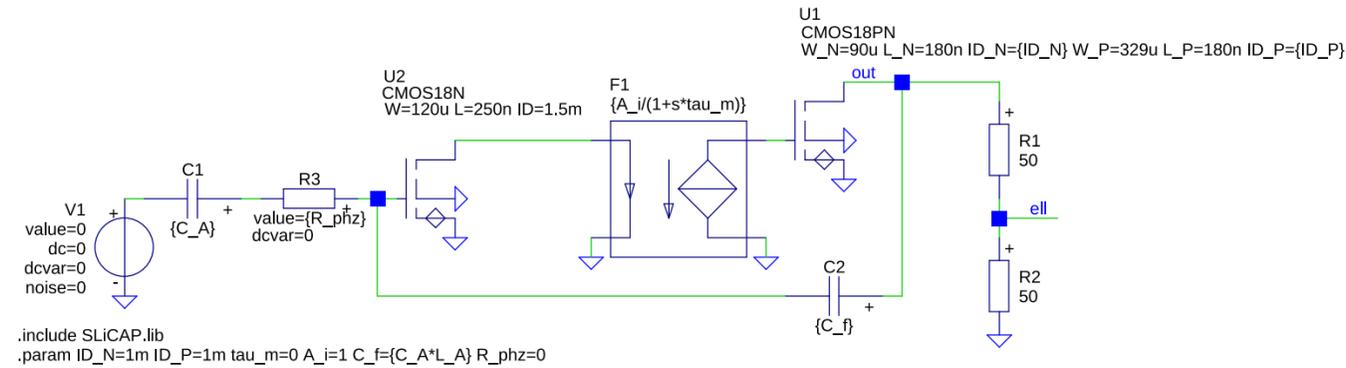
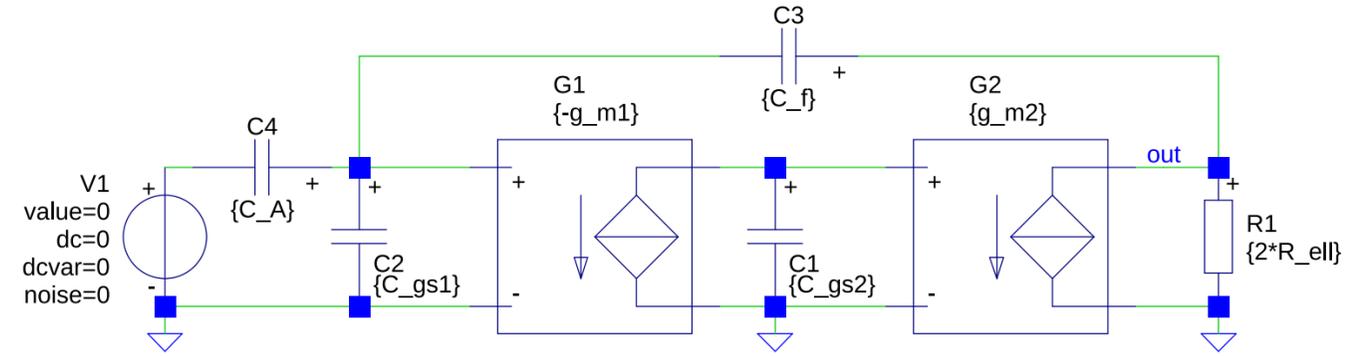
# Active antenna with multiple-stage controller

## Stepwise design of

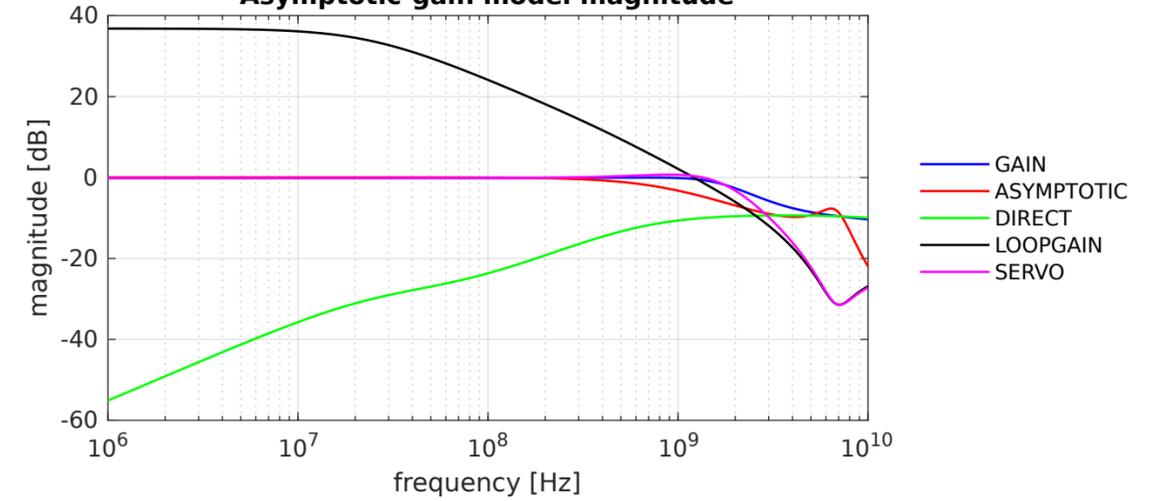
Drive capability

Noise performance

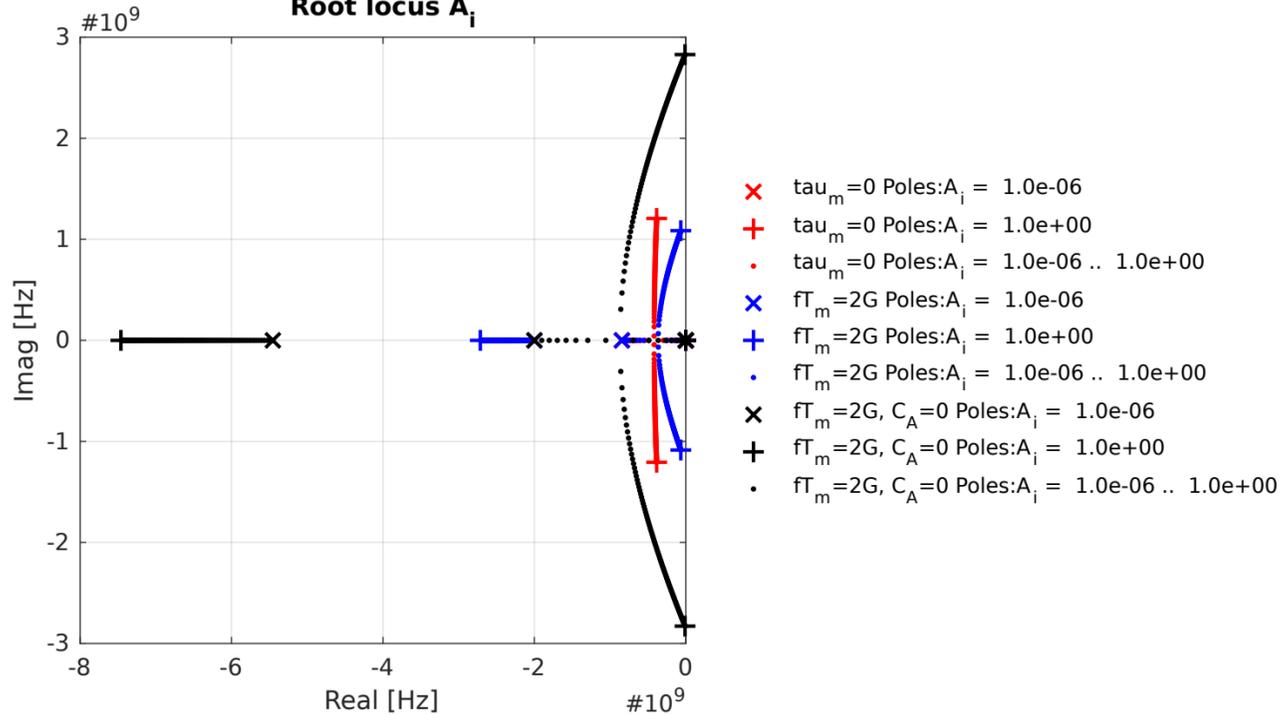
Bandwidth



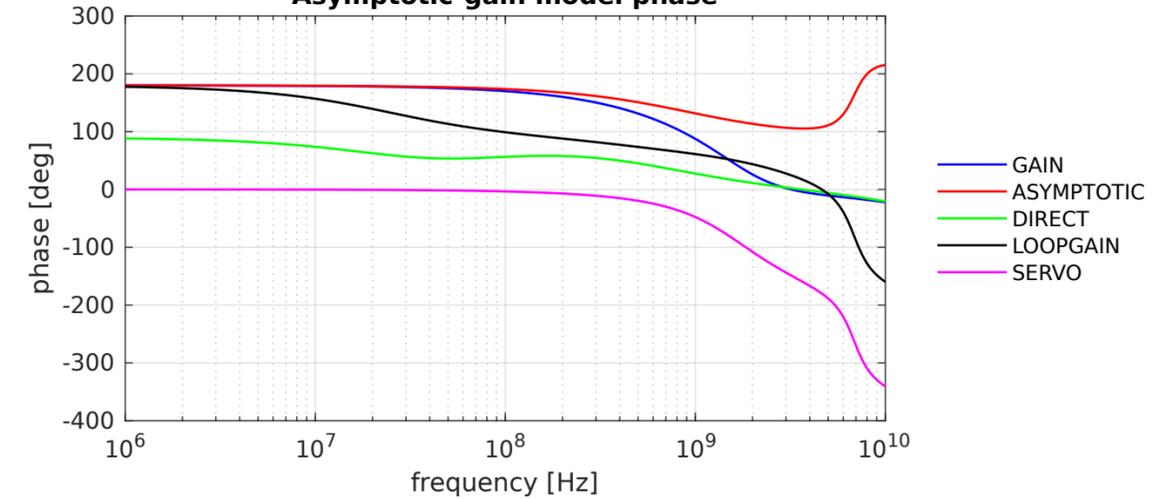
Asymptotic-gain model magnitude



Root locus A<sub>i</sub>



Asymptotic-gain model phase



## Phantom zero compensation

Recap of concept EE3C11  
Application in transistor circuits

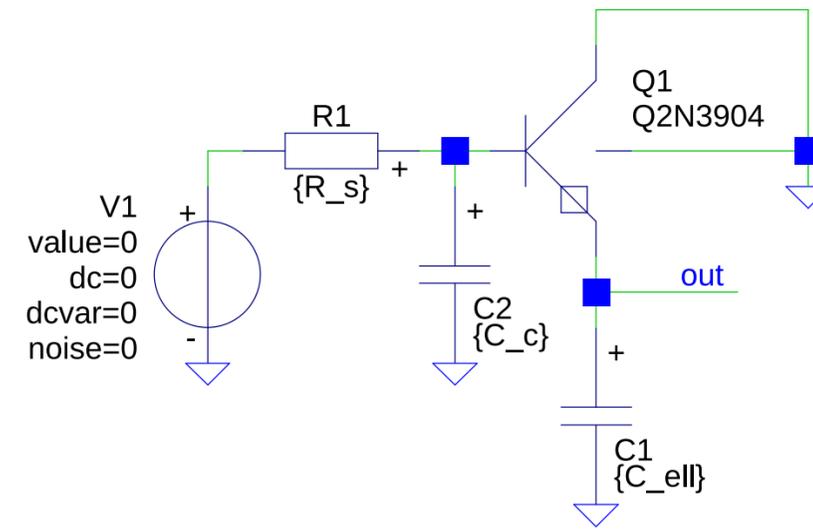
## Pole-splitting

"Miller compensation"

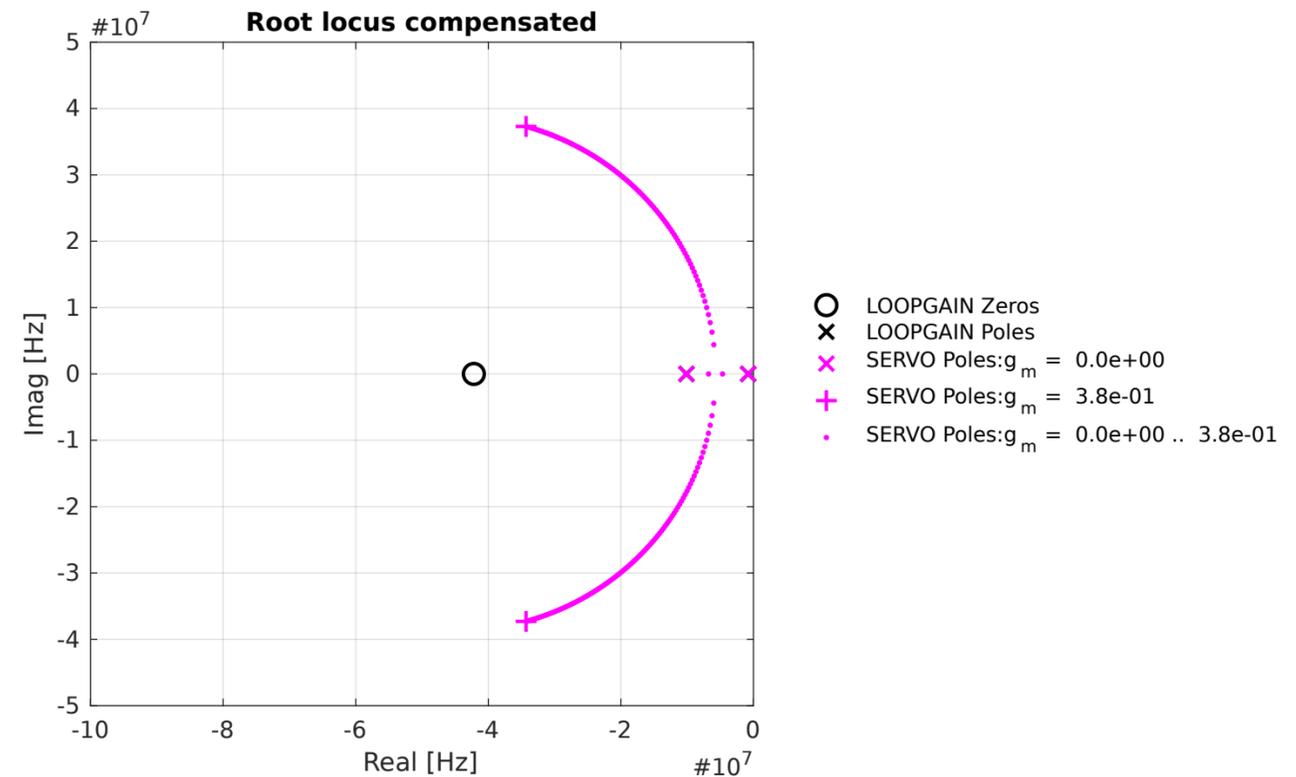
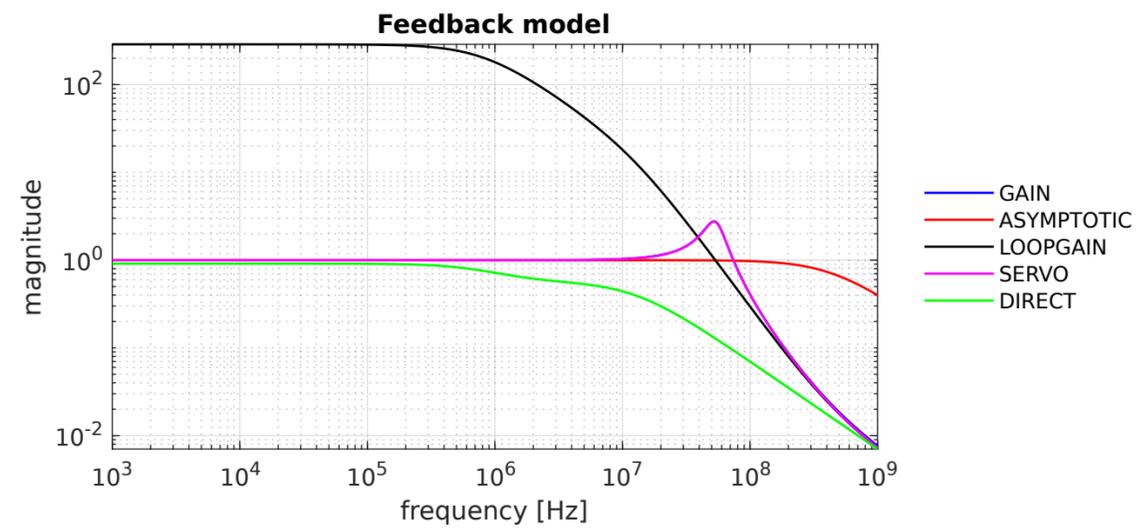
## Pole-zero canceling

## Resistive broadbanding

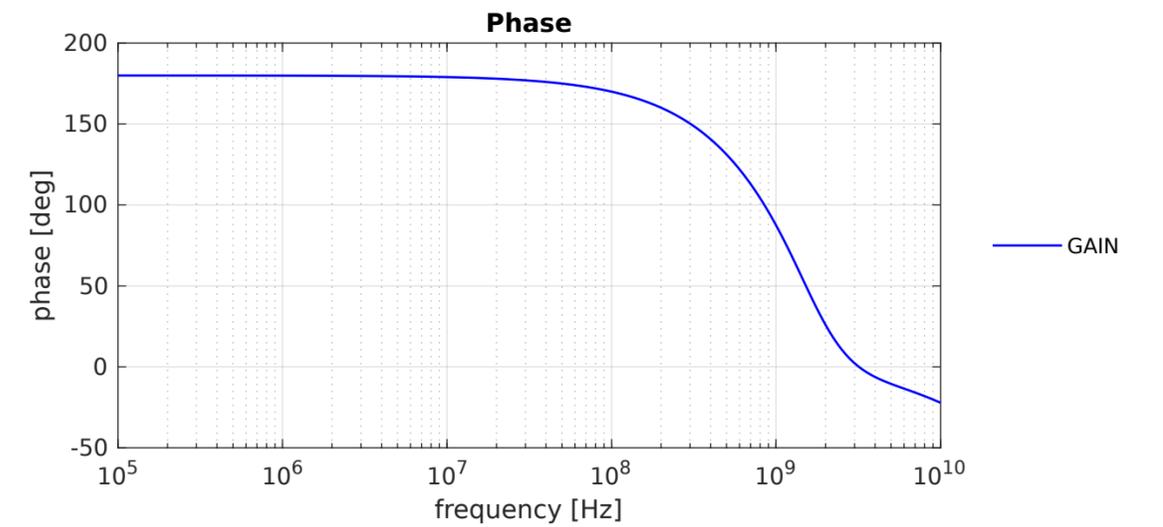
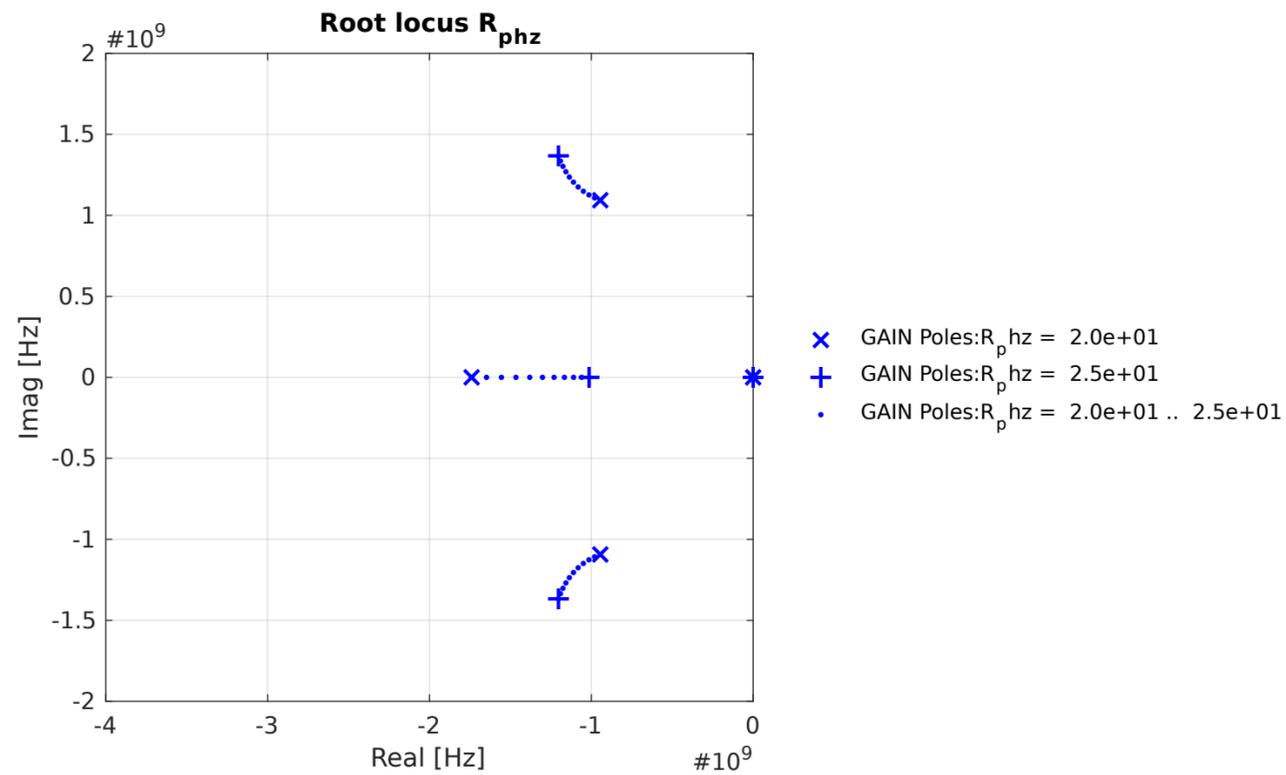
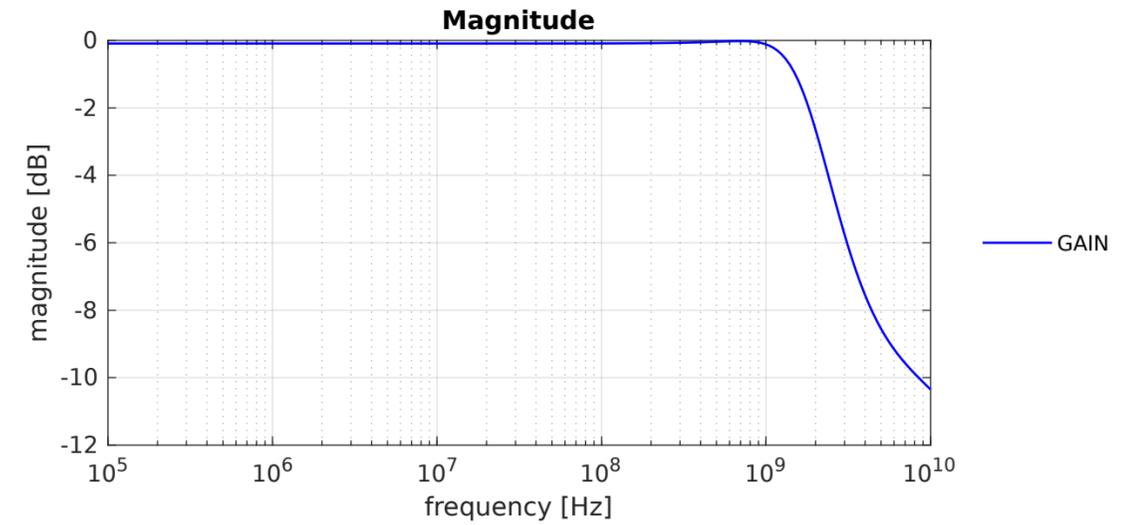
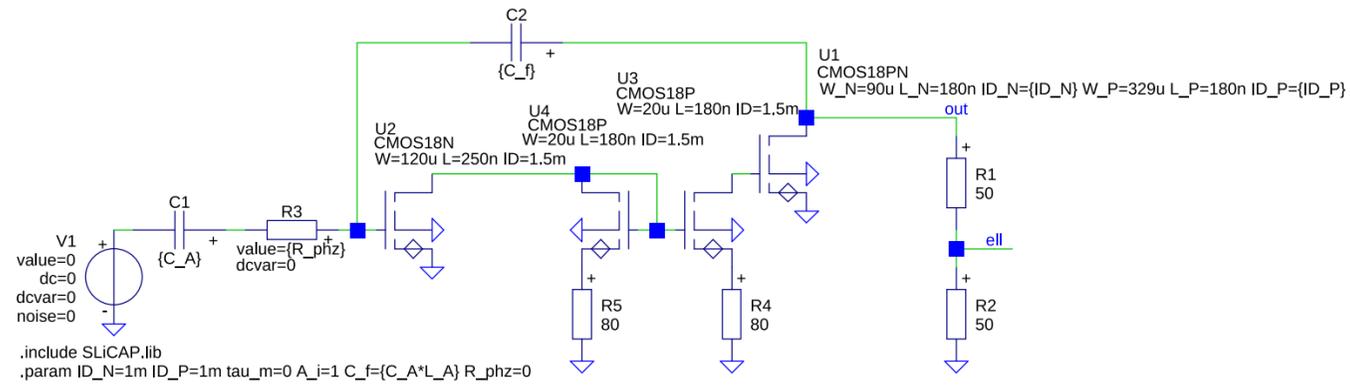
## Bandwidth limitation



```
.model Q2N3904 QV gpi={g_m/beta_AC} gm={g_m} go={g_o} rb={r_b} cpi={c_pi} cbc={c_bc}
.param g_m=377m beta_AC=323 r_b=20 c_pi=145p c_bc=1.7p g_o=90.9u
.param R_s=200 C_ell=100p C_c=0
```



# Active antenna design frequency response



# Biassing and design of bias sources

Design of biasing concepts

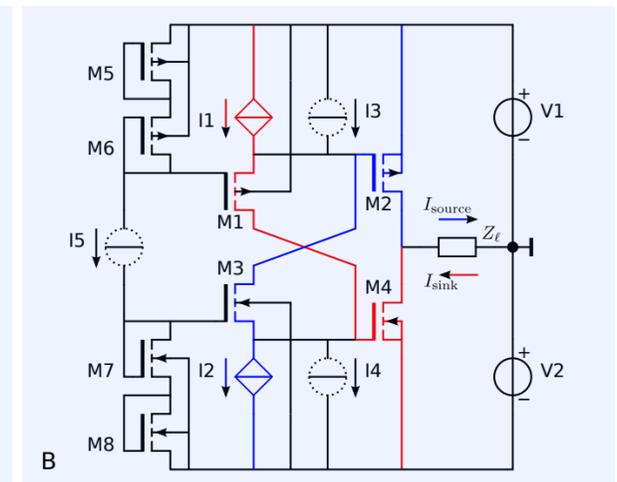
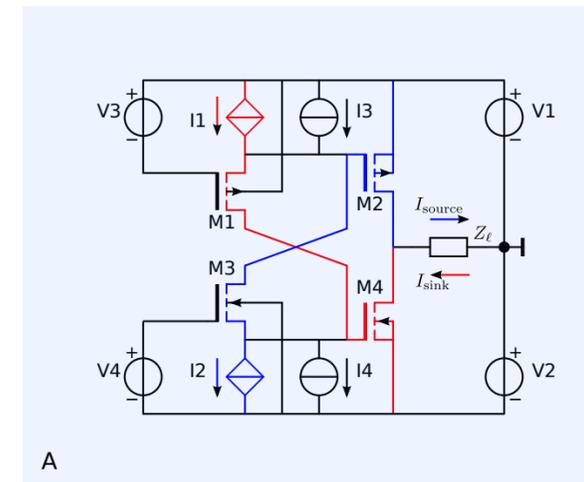
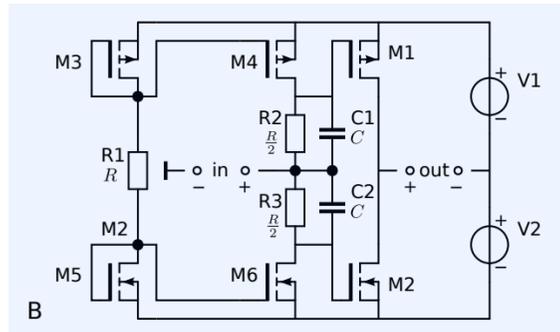
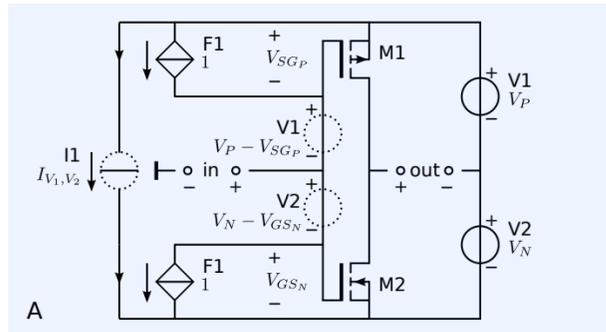
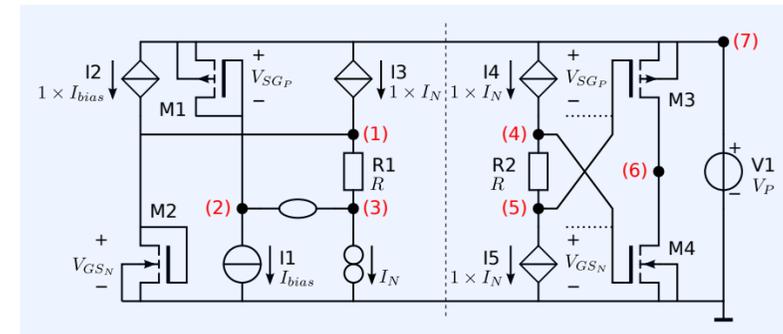
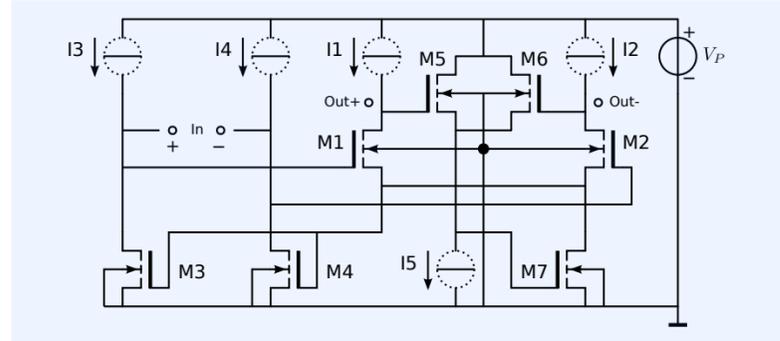
Minimization of floating voltage sources

Common mode biasing

Implementation of bias sources

Evaluation of biasing errors

Application of error reduction techniques



# Completion design active antenna

